

DESCRIPTION

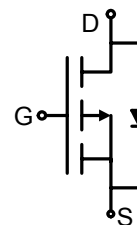
The SSF3341L uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications.

GENERAL FEATURES

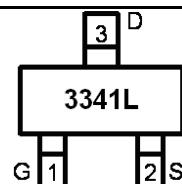
- $V_{DS} = -30V, I_D = -4.2A$
 $R_{DS(ON)} < 120m\Omega @ V_{GS} = -2.5V$
 $R_{DS(ON)} < 65m\Omega @ V_{GS} = -4.5V$
 $R_{DS(ON)} < 50m\Omega @ V_{GS} = -10V$
- High Power and current handling capability
- Lead free product is acquired
- Surface Mount Package

Application

- PWM applications
- Load switch
- Power management



Schematic diagram



Marking and pin Assignment



SOT-23-3 top view

PACKAGE MARKING AND ORDERING INFORMATION

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
3341L	SSF3341L	SOT-23-3	Ø180mm	8 mm	3000 units

ABSOLUTE MAXIMUM RATINGS(TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	±12	V
Drain Current-Continuous@ Current-Pulsed (Note 1)	$I_D (25^\circ C)$	-4.2	A
	$I_D (70^\circ C)$	-3.5	A
	I_{DM}	-30	A
Maximum Power Dissipation	P_D	1	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	90	°C/W
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ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-24V, V_{GS}=0V$			-1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 12V, V_{DS}=0V$			±100	nA

ON CHARACTERISTICS (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-0.7		-2	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-4.2A		42	50	mΩ
		V _{GS} =-4.5V, I _D =-4A		53	65	
		V _{GS} =-2.5V, I _D =-1A		80	120	
Forward Transconductance	g _{FS}	V _{DS} =-5V, I _D =-5A		10		S
DYNAMIC CHARACTERISTICS (Note4)						
Input Capacitance	C _{ISS}	V _{DS} =-15V, V _{GS} =0V, F=1.0MHz		950		PF
Output Capacitance	C _{OSS}			120		PF
Reverse Transfer Capacitance	C _{RSS}			70		PF
SWITCHING CHARACTERISTICS (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =-15V, I _D =-3.2A V _{GS} =-10V, R _{GEN} =6Ω		6.5		nS
Turn-on Rise Time	t _r			3		nS
Turn-Off Delay Time	t _{d(off)}			30		nS
Turn-Off Fall Time	t _f			12		nS
Total Gate Charge	Q _g	V _{DS} =-15V, I _D =-4A, V _{GS} =-4.5V		9.6		nC
Gate-Source Charge	Q _{gs}			2		nC
Gate-Drain Charge	Q _{gd}			2.6		nC
DRAIN-SOURCE DIODE CHARACTERISTICS						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =-1A			-1.2	V

NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on 1in² FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production testing.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

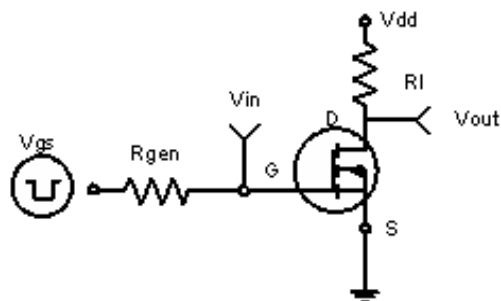


Figure 1: Switching Test Circuit

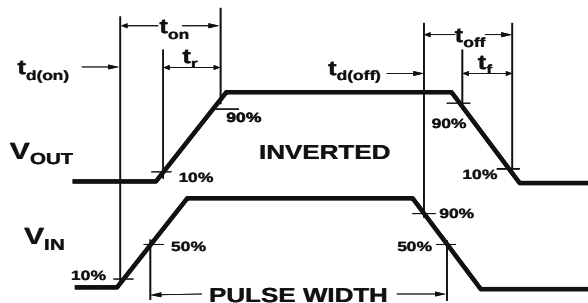


Figure 2: Switching Waveforms

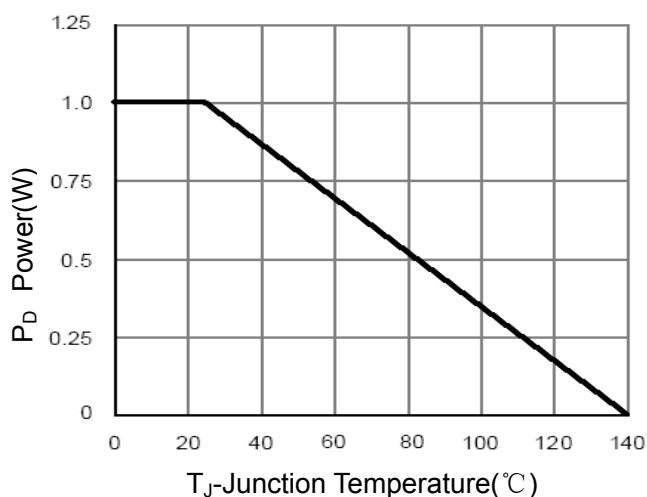


Figure 3 Power Dissipation

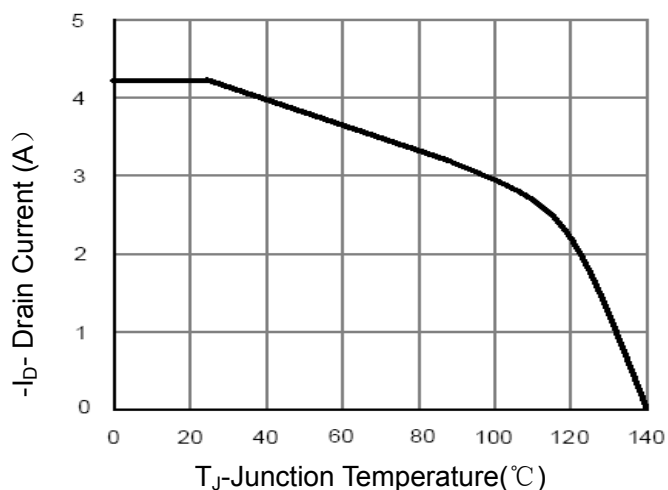


Figure 4 Drain Current

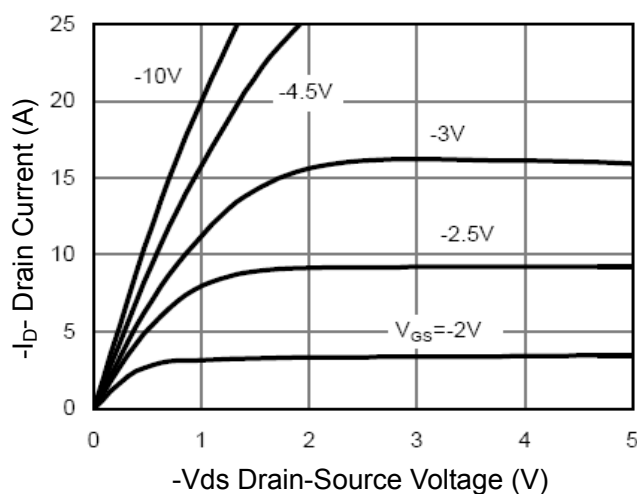


Figure 5 Output CHARACTERISTICS

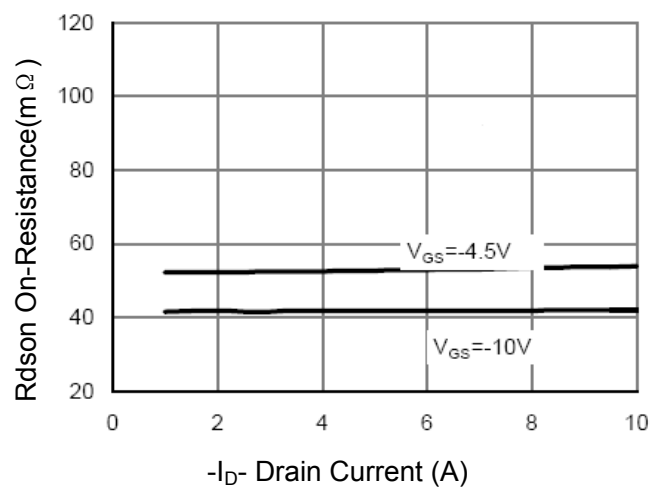
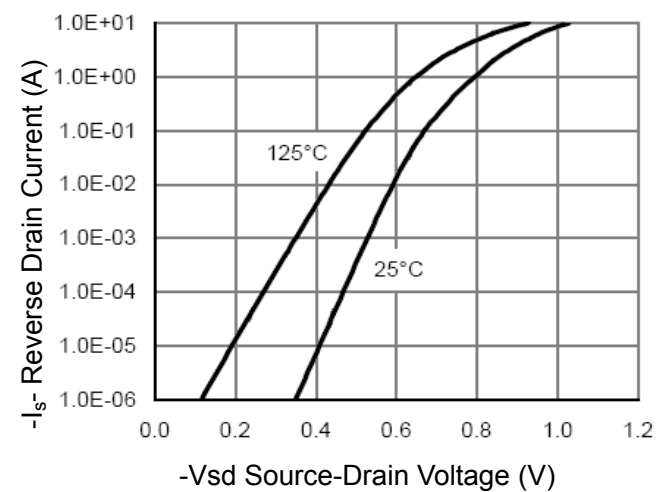
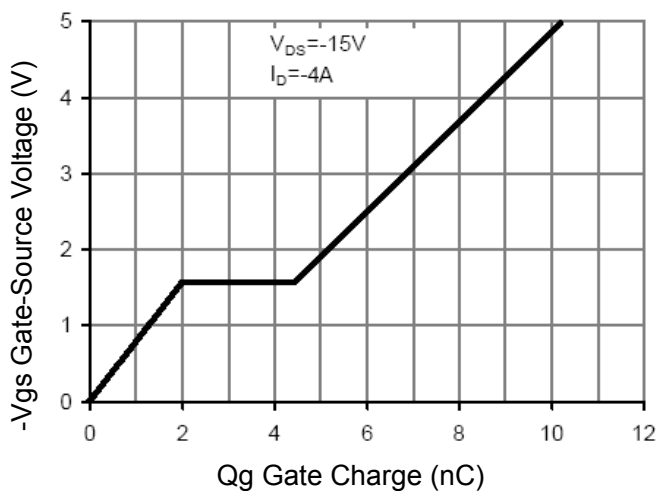
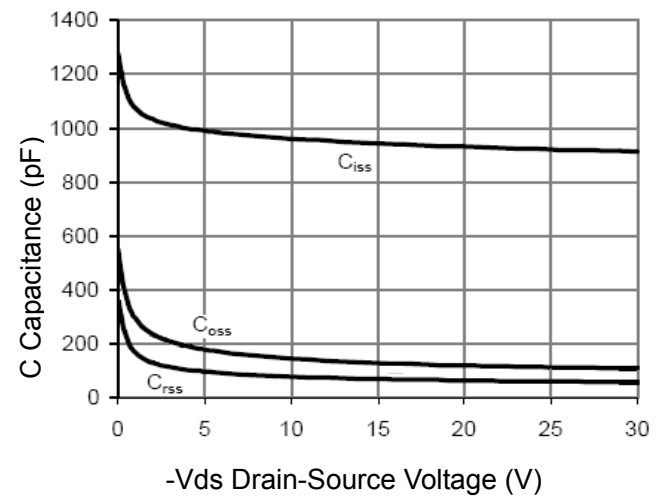
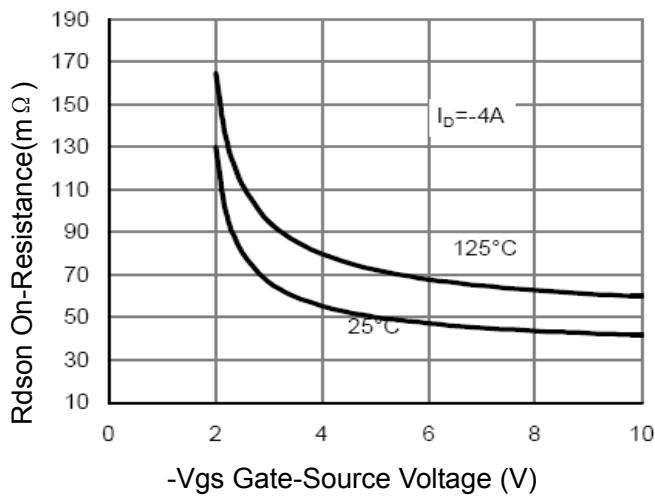
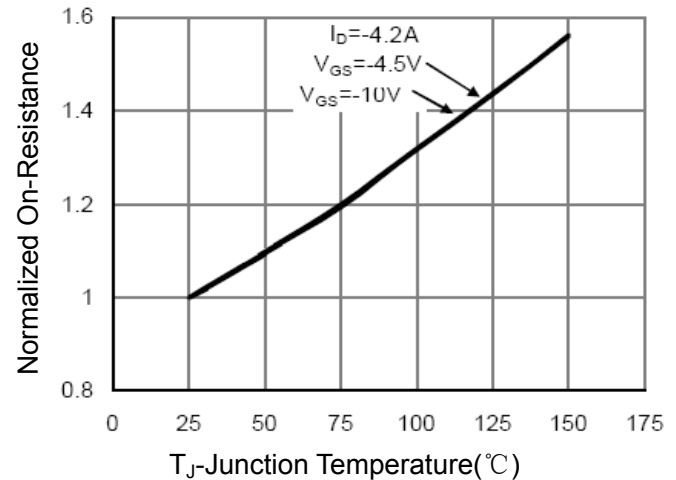
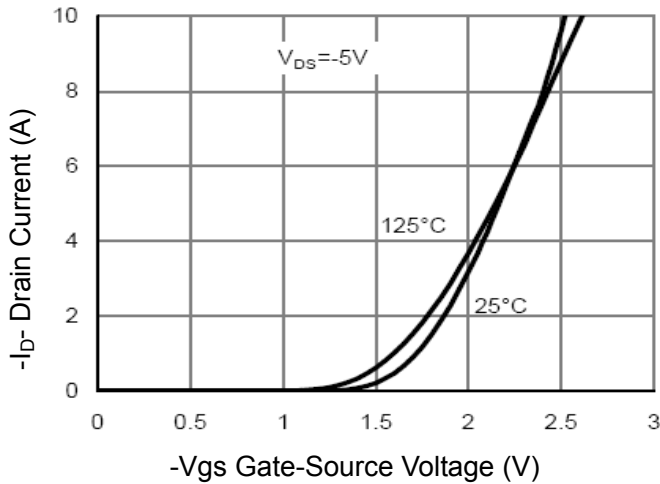


Figure 6 Drain-Source On-Resistance



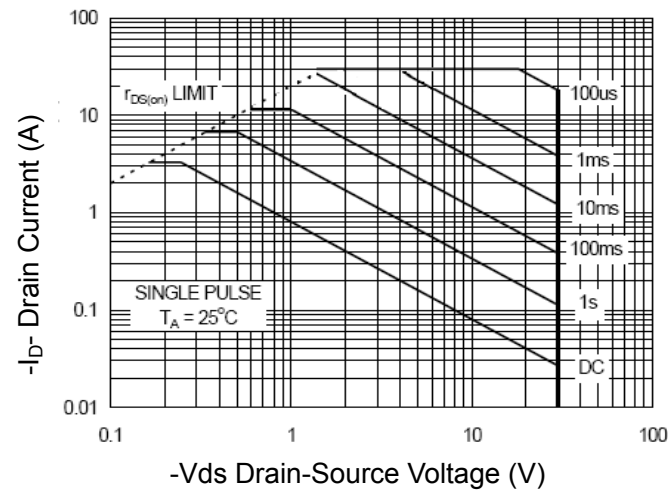


Figure 13 Safe Operation Area

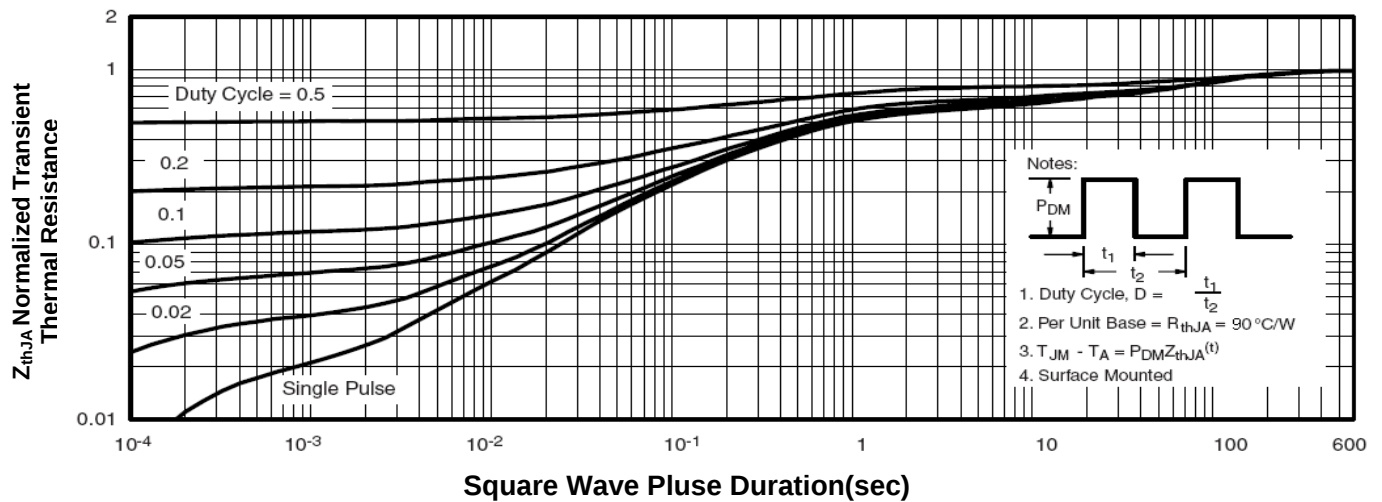
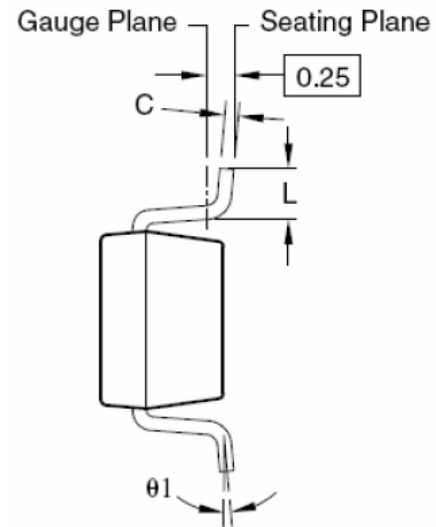
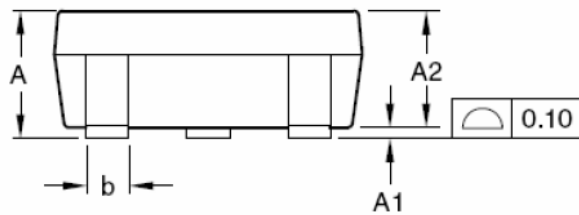
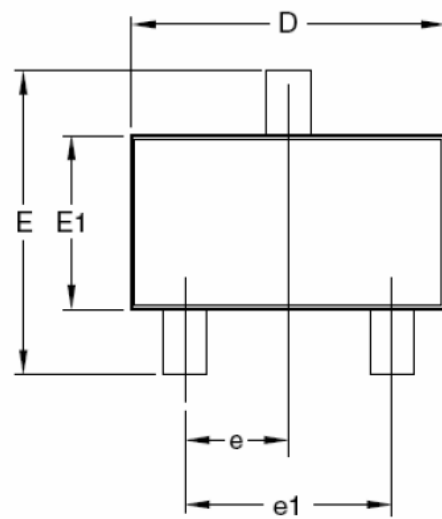
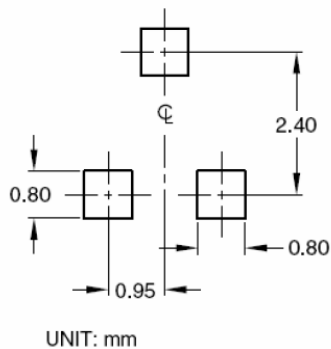


Figure 14 Normalized Maximum Transient Thermal Impedance

SOT23-3 PACKAGE INFORMATION



RECOMMENDED LAND PATTERN



Dimensions in millimeters

Symbols	Min.	Nom.	Max.
A	0.90	—	1.25
A1	0.00	—	0.13
A2	0.70	1.00	1.15
b	0.30	0.40	0.50
C	0.08	0.13	0.20
D	2.80	2.90	3.10
E	2.60	2.80	3.00
E1	1.40	1.60	1.80
e	0.95 BSC		
e1	1.90 BSC		
L	0.30	—	0.60
θ1	0°	5°	8°

Dimensions in inches

Symbols	Min.	Nom.	Max.
A	0.035	—	0.049
A1	0.000	—	0.005
A2	0.028	0.039	0.045
b	0.012	0.016	0.020
C	0.003	0.005	0.008
D	0.110	0.114	0.122
E	0.102	0.110	0.118
E1	0.055	0.063	0.071
e	0.037 BSC		
e1	0.075 BSC		
L	0.012	—	0.024
θ1	0°	5°	8°

NOTES:

1. Tolerance $\pm 0.10\text{mm}$ (4 mil) unless otherwise specified
2. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
3. Dimension L is measured in gauge plane.
4. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.

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